

Si Photo-diode Chip—TK0N40PDN

1. Scope

- The specification applies to NIP silicon photo-diode chips.
- Type : TK0N40PDN.

2. Structure

- NIP planar type.
- Electrode topside (cathode) : Aluminum.
backside (anode) : Gold alloy.

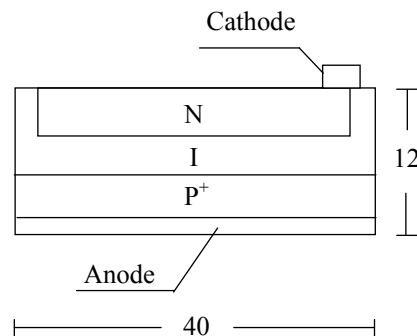
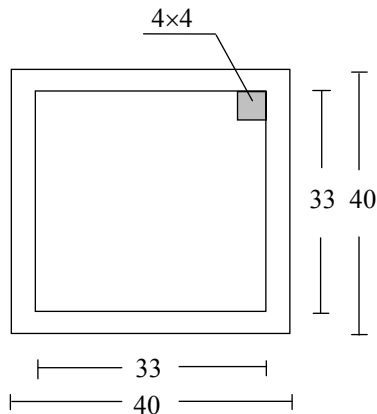
3. Size

- Chip size : $40\text{mil} \times 40\text{mil} \pm 2\text{mil}$ ($1.010\text{mm} \times 1.010\text{mm} \pm 0.05\text{mm}$)
- Thickness : $12\text{mil} \pm 1\text{mil}$ ($0.300\text{mm} \pm 0.025\text{mm}$)
- Active area : $33\text{mil} \times 33\text{mil}$ ($0.840\text{mm} \times 0.840\text{mm}$)
- Pattern drawing : per fig. 1

4. Electro-Optical Characteristics

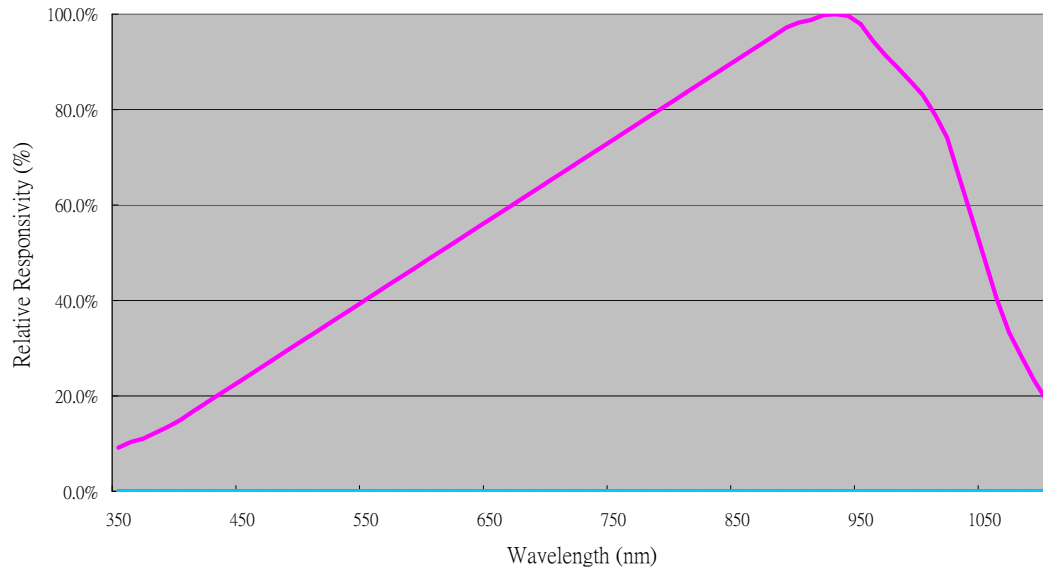
($T_a = +25^\circ\text{C}$)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit.
Forward Voltage	V_F	$I_F = 10\text{mA}$, $H=0$	0.5		1.3	V
Reverse Dark Current	I_D	$V_R = 10\text{V}$, $H=0$			50	nA
Reverse Breakdown Voltage	V_{BR}	$I_R = 100\mu\text{A}$, $H=0$	35			V
Light Current	I_L	$V_R = 5\text{V}$, H as $1\text{mw}/\text{cm}^2 @ 940\text{nm}$	29	31	33	μA



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5. Spectral Response



Unit : mil

fig. 1

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